

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently amended) A polishing slurry for CMP of Cu, which comprises:
a first complexing agent containing a ~~heterocyclic compound which is capable of forming a water insoluble complex with Cu~~ guinaldinic acid; and
a second complexing agent containing a ~~heterocyclic compound which is capable of forming a slightly water soluble or water soluble complex with Cu to thereby provide at least one extra ligand subsequent to formation of the complex~~ quinolinic acid.

2. (Original) The polishing slurry for CMP of Cu according to claim 1, wherein a mixing ratio of said first complexing agent to said second complexing agent is within the range of 2:8 to 8:2 based on weight.

3. (Original) The polishing slurry for CMP of Cu according to claim 1, wherein a mixing ratio of said first complexing agent to said second complexing agent is within the range of 4:6 to 6:4 based on weight.

4-6. (Canceled)

7. (Original) The polishing slurry for CMP of Cu according to claim 1, which further comprises an oxidizing agent selected from the group consisting of persulfuric acid, ammonium persulfate and hydrogen peroxide.

8. (Original) The polishing slurry for CMP of Cu according to claim 1, which further comprises polishing particles comprising a material selected from the group consisting of silica, alumina, zirconia and ceria.

9. (Original) The polishing slurry for CMP of Cu according to claim 1, which further comprises a polishing rate promoting agent selected from the group consisting of glycine and alanine.

10. (Original) The polishing slurry for CMP of Cu according to claim 1, which further comprises a surfactant.

11-20. (Canceled)

21. (New) The polishing slurry for CMP of Cu according to claim 8, wherein said polishing particles comprising colloidal silica.

22. (New) The polishing slurry for CMP of Cu according to claim 10, wherein said surfactant is one selected from the group consisting of potassium dodecylbenzenesulfonate, and ammonium dodecylbenzenesulfonate.

23. (New) The polishing slurry for CMP of Cu according to claim 10, wherein said surfactant is acetylene diol-based nonion.

24. (New) The polishing slurry for CMP of Cu according to claim 10, wherein said surfactant comprises potassium dodecylbenzenesulfonate and acetylene diol-based nonion.